NSN 5961-01-624-7504

No Fiig: A110a0



Transistor - Page 1 of 1 View Online at https://aerobasegroup.com/nsn/5961-01-624-7504 **Overall Length:** Between 1.335 inches and 1.345 inches **Overall Height:** Between 0.125 inches and 0.170 inches Overall Width: Between 0.380 inches and 0.390 inches **Function For Which Designed:** Programmable transistor **Internal Configuration:** Field effect **Electrode Internally-electrically Connected To Case:** Gate **Features Provided:** Gold plated leads Voltage Rating In Volts Per Characteristic: 65.0 drain to source voltage **Current Rating Per Characteristic:** 10.0 microamperes zero-gate-voltage drain current **Power Rating Per Characteristic:** 298.0 watts total device dissipation **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Product Name:** Rf power field effect transistor **Special Features:** In tape and reel, r3 suffix= 250 units per 56mm, 13 inch reel; rohs compliant; designed for gsm and gsm edge base station applications with frequencies from 921 to 960 mhz; designed for maximum gain and instertion phase flatness; high gain and broadband performance of these devices make them ideal for large signal, common source amplifier applications in 28 volt base stations; high efficiency; high linearity; integrated esd protection **Terminal Type And Quantity:** 3 pin Shelf Life: N/a **Unit Of Measure:** Demilitarization: